

FDT86256

N-Channel PowerTrench® MOSFET 150 V, 1.2 A, 845 mΩ

Features

- Max $r_{DS(on)}$ = 845 mΩ at $V_{GS} = 10$ V, $I_D = 1.2$ A
- Max $r_{DS(on)}$ = 1280 mΩ at $V_{GS} = 6.0$ V, $I_D = 1.0$ A
- Very low Q_g and Q_{gd} compared to competing trench technologies
- Fast switching speed
- 100% UIL Tested
- RoHS Compliant

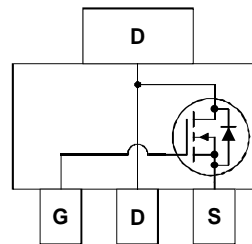
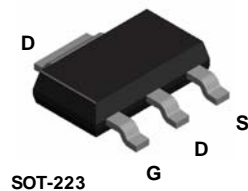


General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and switching loss. G-S zener has been added to enhance ESD voltage level.

Applications

- DC-DC conversion
- Inverter
- Synchronous Rectifier



MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25$ °C	3	A
	-Continuous (Silicon limited) $T_C = 25$ °C	2.5	
	-Continuous $T_A = 25$ °C (Note 1a)	1.2	
	-Pulsed	2	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	1	mJ
P_D	Power Dissipation $T_C = 25$ °C	10	W
	Power Dissipation $T_A = 25$ °C (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	12	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	55	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
86256	FDT86256	SOT-223	13 "	12 mm	2500 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		100		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2	3.5	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-8		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 1.2\text{ A}$		695	845	m Ω
		$V_{GS} = 6\text{ V}, I_D = 1.0\text{ A}$		912	1280	
		$V_{GS} = 10\text{ V}, I_D = 1.2\text{ A}, T_J = 125\text{ }^\circ\text{C}$		1298	1367	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 1.2\text{ A}$		0.3		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		55	73	pF
C_{oss}	Output Capacitance			8	11	pF
C_{riss}	Reverse Transfer Capacitance			1	1.4	pF
R_g	Gate Resistance			1.3		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 75\text{ V}, I_D = 1.2\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		2.7	10	ns
t_r	Rise Time			1.7	10	ns
$t_{d(off)}$	Turn-Off Delay Time			4.8	10	ns
t_f	Fall Time			2.6	10	ns
$Q_{g(TOT)}$	Total Gate Charge		$V_{GS} = 0\text{ V to } 10\text{ V}$	$V_{DD} = 75\text{ V},$ $I_D = 1.2\text{ A}$	1.2	2.0
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V to } 6\text{ V}$	0.8		1.0	
Q_{gs}	Gate to Source Charge		0.4			nC
Q_{gd}	Gate to Drain "Miller" Charge		0.3			nC

Drain-Source Diode Characteristics

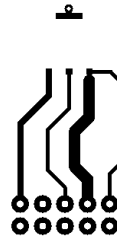
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.2\text{ A}$ (Note 2)		0.9	1.3	V
		$V_{GS} = 0\text{ V}, I_S = 1.0\text{ A}$ (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 1.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		47	75	ns
Q_{rr}	Reverse Recovery Charge			24	38	nC

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $55\text{ }^\circ\text{C/W}$ when mounted on a 1 in^2 pad of 2 oz copper



b) $118\text{ }^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < $300\text{ }\mu\text{s}$, Duty cycle < 2.0 %.
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 1\text{ A}$, $V_{DD} = 150\text{ V}$, $V_{GS} = 10\text{ V}$.
- The diode connected between gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

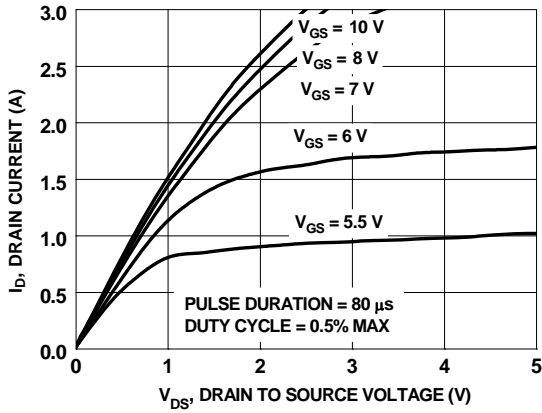


Figure 1. On-Region Characteristics

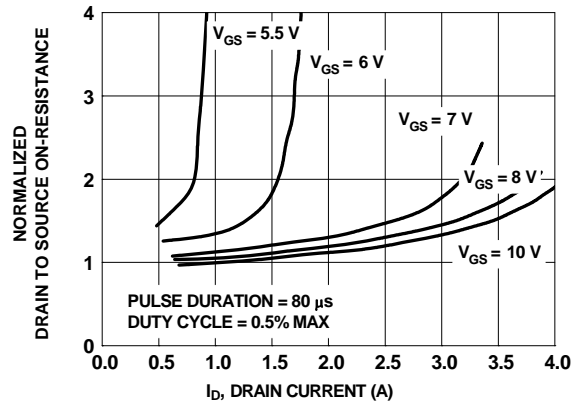


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

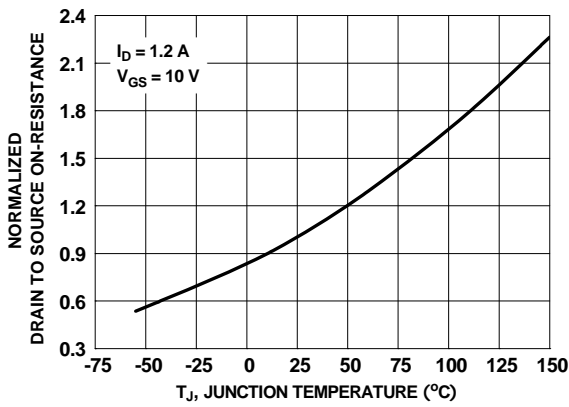


Figure 3. Normalized On-Resistance vs Junction Temperature

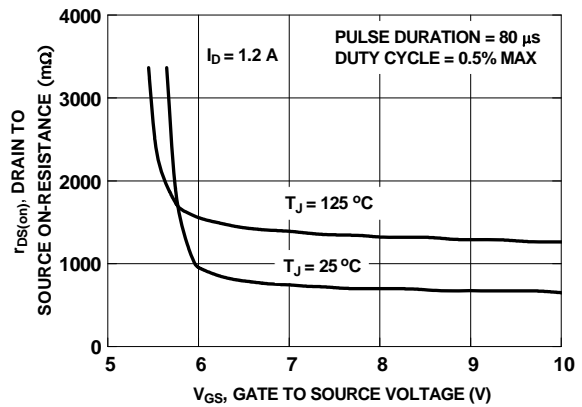


Figure 4. On-Resistance vs Gate to Source Voltage

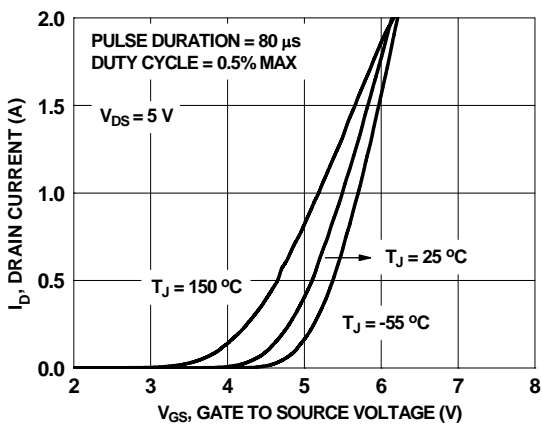


Figure 5. Transfer Characteristics

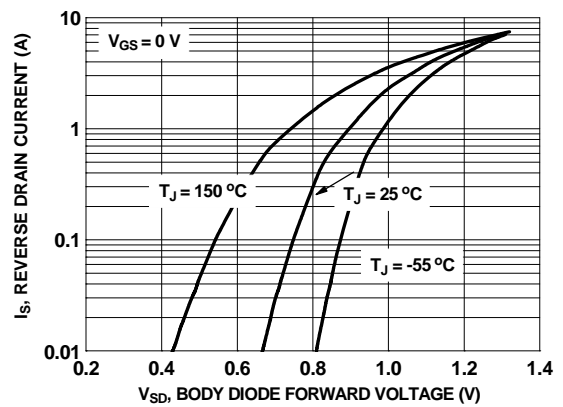


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

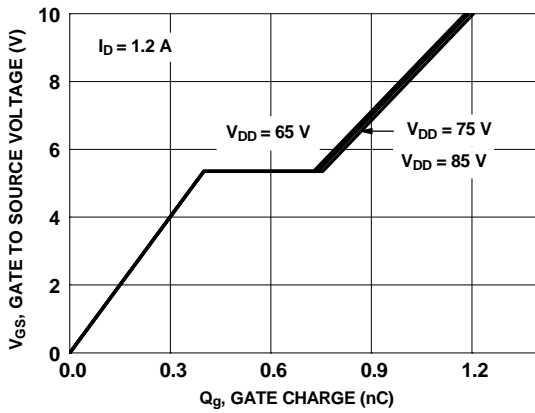


Figure 7. Gate Charge Characteristics

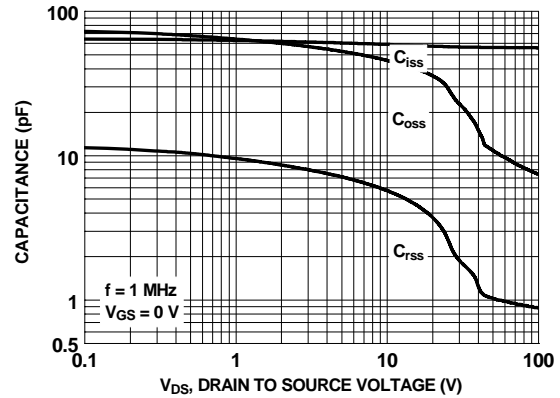


Figure 8. Capacitance vs Drain to Source Voltage

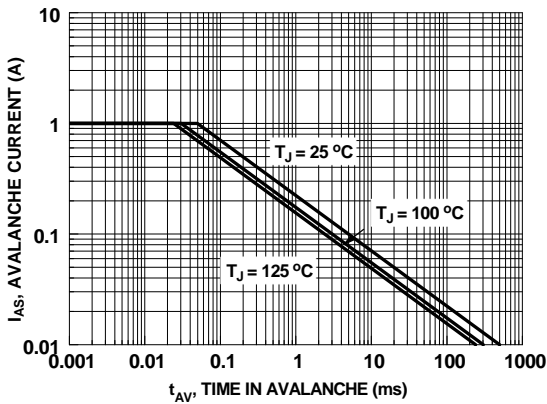


Figure 9. Unclamped Inductive Switching Capability

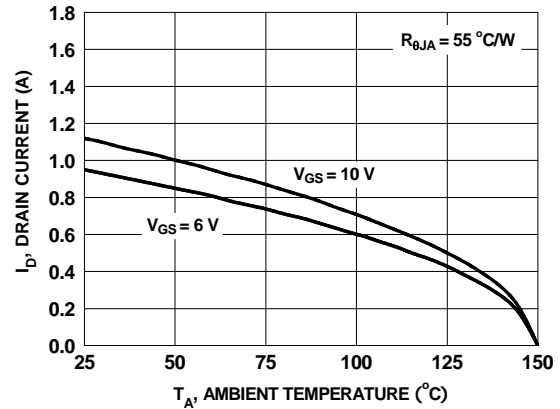


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

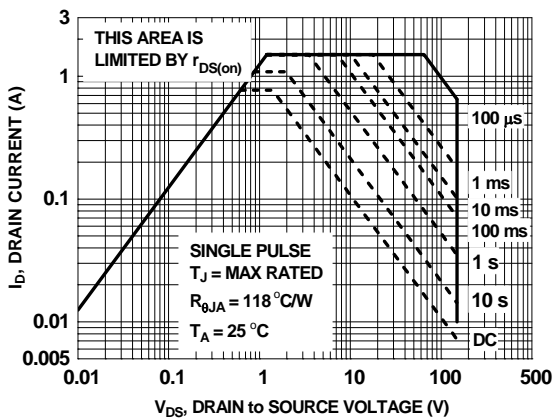


Figure 11. Forward Bias Safe Operating Area

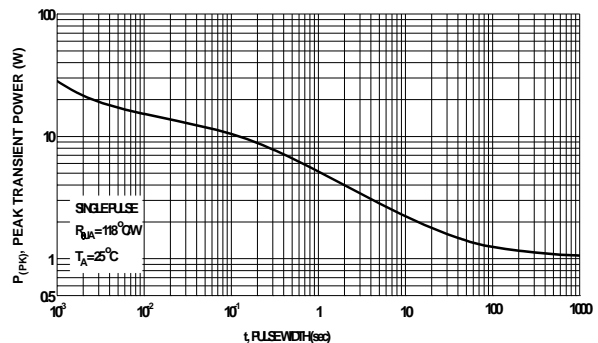
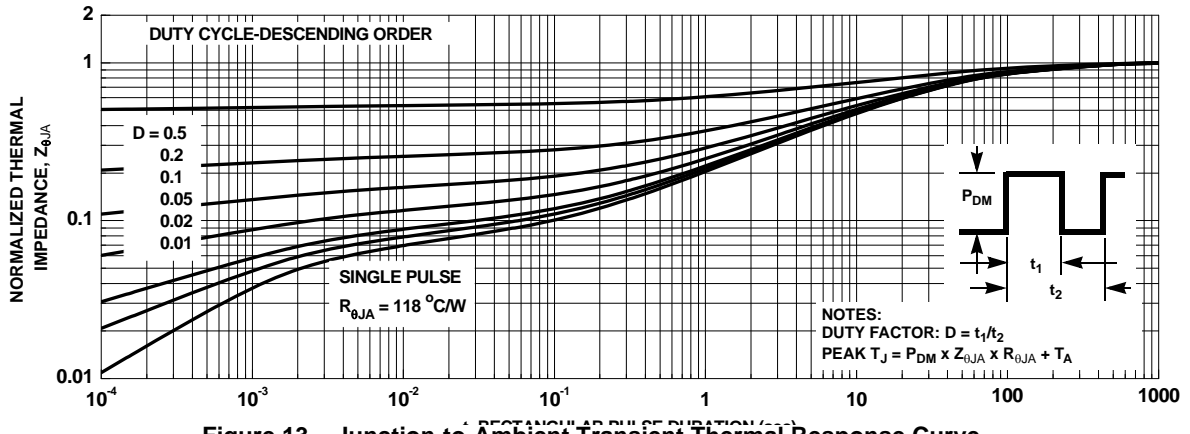


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

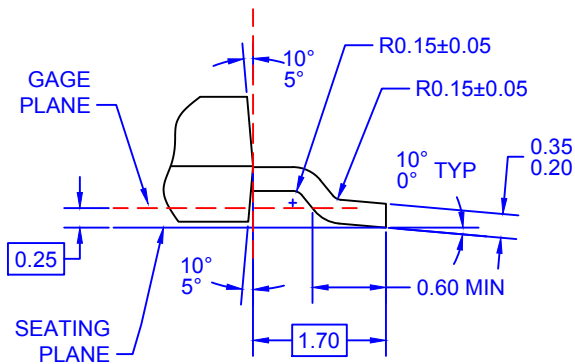




LAND PATTERN RECOMMENDATION



SEE DETAIL A



DETAIL A
SCALE: 2:1

- NOTES: UNLESS OTHERWISE SPECIFIED
 A) DRAWING BASED ON JEDEC REGISTRATION TO-261C, VARIATION AA.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 E) LANDPATTERN NAME: SOT230P700X180-4BN
 F) DRAWING FILENAME: MKT-MA04AREV3



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